SANYO

No.3099

2SC4493

NPN Triple Diffused Planar Silicon Transistor

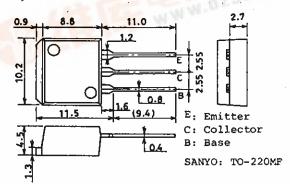
High-Voltage Amp, High-Voltage Switching Applications

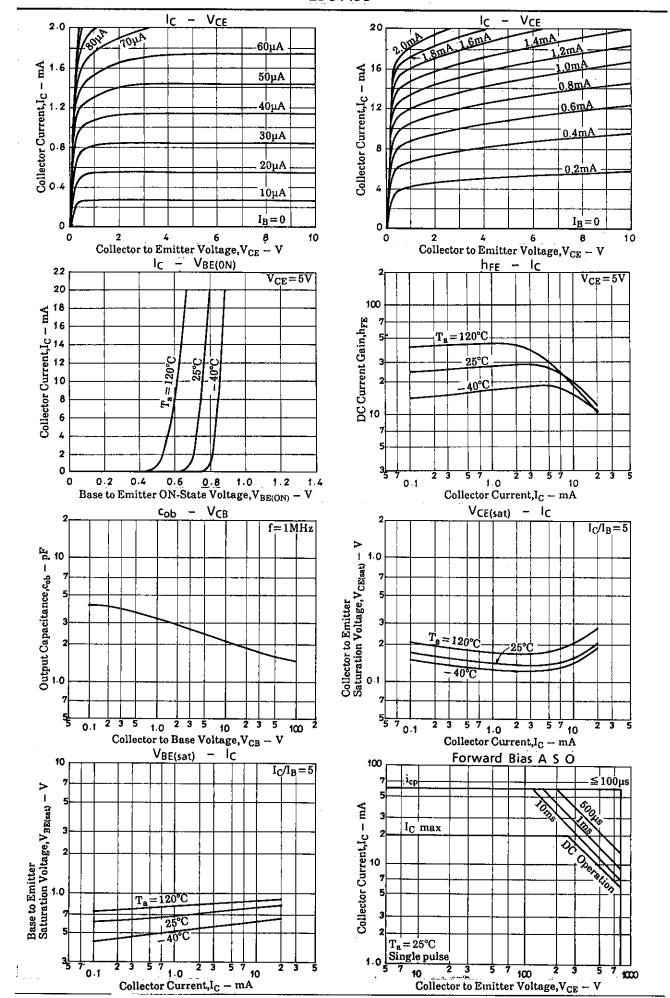
## Features

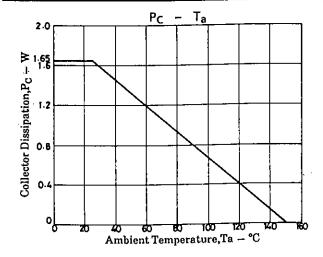
- . High breakdown voltage
- · Small cob
- · High reliability (adoption of HVP process)
- · Intended for high-density mounting (Suitable for sets whose height is restricted)

	Absolute Maximum Ratings at Ta = 25°C			unit		
	Collector to Base Voltage	$V_{\mathrm{CBO}}$		800	V	
	Collector to Emitter Voltage	$v_{ceo}$		800	V	
	Emitter to Base Voltage	$V_{EBO}$		7	V	
	Collector Current	$I_{\mathbf{C}}$		20	mA	
	Peak Collector Current	i <sub>cp</sub>		60	mA	
	Collector Dissipation	$P_{\mathbf{C}}^{\mathbf{r}}$		1.65	W	
	Junction Temperature	Тj		150	°C	
	Storage Temperature	Tstg		-55  to  +150	°C	
Electrical Characteristics at Ta=25°C min						unit
	Collector Cutoff Current	Ісво	$V_{CB} = 800 V, I_{E} = 0$		1	μA
	Emitter Cutoff Current	IEBO	$V_{EB}=5V,I_C=0$		1	μA
	DC Current Gain	$h_{FE}(1)$	$V_{CE}=5V,I_{C}=2mA$	20	50	
		$h_{FE}(2)$	$V_{CE}=5V,I_{C}=10mA$	10		
	Gain-Bandwidth Product	$\mathbf{f_T}$	$V_{CE} = 10V, I_C = 2mA$	40		MHz
	C-E Saturation Voltage	$V_{\mathrm{CE}(\mathrm{sat})}$	$I_C = 10 \text{mA}, I_B = 2 \text{mA}$		50 F	V
	B-E Saturation Voltage	$V_{\mathrm{BE}(\mathrm{sat})}$	$I_C=10\text{mA},I_B=2\text{mA}$		1.5	V
	C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	800		V
	C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_C = 1 \text{mA}, R_{BE} = \infty$	800		V
	E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	$I_E = 100 \mu A, I_C = 0$	7		V
	Output Capacitance	cob	$V_{CB} = 100V, f = 1MHz$	1.6		pF

## Package Dimensions 2049B (unit: mm)







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